



JST80IS-1600BW 80A TRIACs

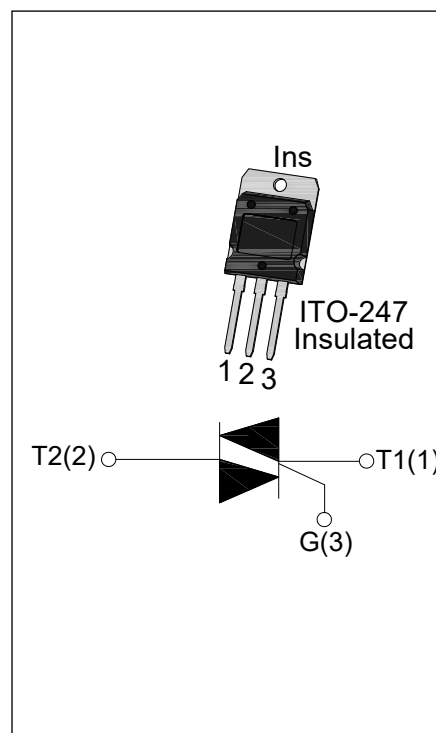
Rev.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JST80IS-1600BW triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, especially recommended for use on inductive load. From all three pins to external heatsink, JST80IS-1600BW triac provides an insulation voltage of 2500 V_{RMS}. Package ITO-247 is RoHS compliant. (2011/65/EU)

MAIN FEATURES

Symbol	Value	Unit
I _{T(RMS)}	80	A
V _{DRM} / V _{RRM}	1600	V



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T _{stg}	-40-150	°C
Operating junction temperature range	T _j	-40-125	°C
Repetitive peak off-state voltage (T _j =25°C)	V _{DRM}	1600	V
Repetitive peak reverse voltage (T _j =25°C)	V _{RRM}	1600	V
RMS on-state current ITO-247(Ins) (T _C =85°C)	I _{T(RMS)}	80	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I _{TSM}	800	A
I ² t value for fusing (tp=10ms)	I ² t	3200	A ² s
Critical rate of rise of on-state current (I _G = 2 × I _{GT})	dI/dt	100	A/μs
Peak gate current	I _{GM}	8	A
Average gate power dissipation	P _{G(AV)}	2	W
Peak gate power	P _{GM}	10	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX	50	mA
V_{GT}		I - II -III	MAX	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	80	mA
		II		120	
I_H	$I_T=100\text{mA}$		MAX	70	mA
dv/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	1500	V/ μs

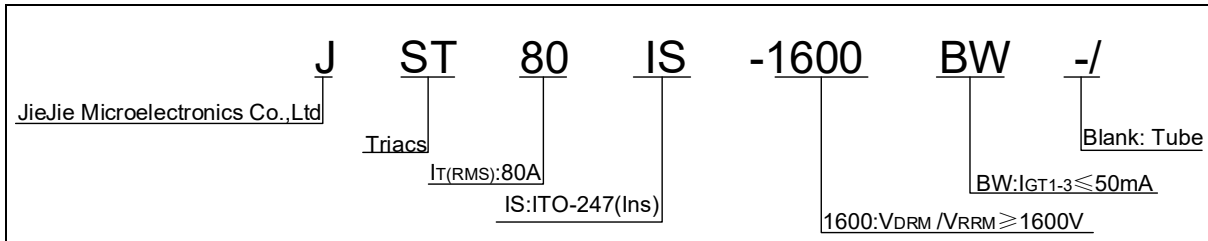
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=120\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	20	μA
I_{RRM}		$T_j=125^\circ\text{C}$	10	mA
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.95	V
R_d	Dynamic resistance	$T_j=125^\circ\text{C}$	8.5	m Ω

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	ITO-247 (Ins)	0.35	$^\circ\text{C}/\text{W}$

ORDERING INFORMATION



MARKING

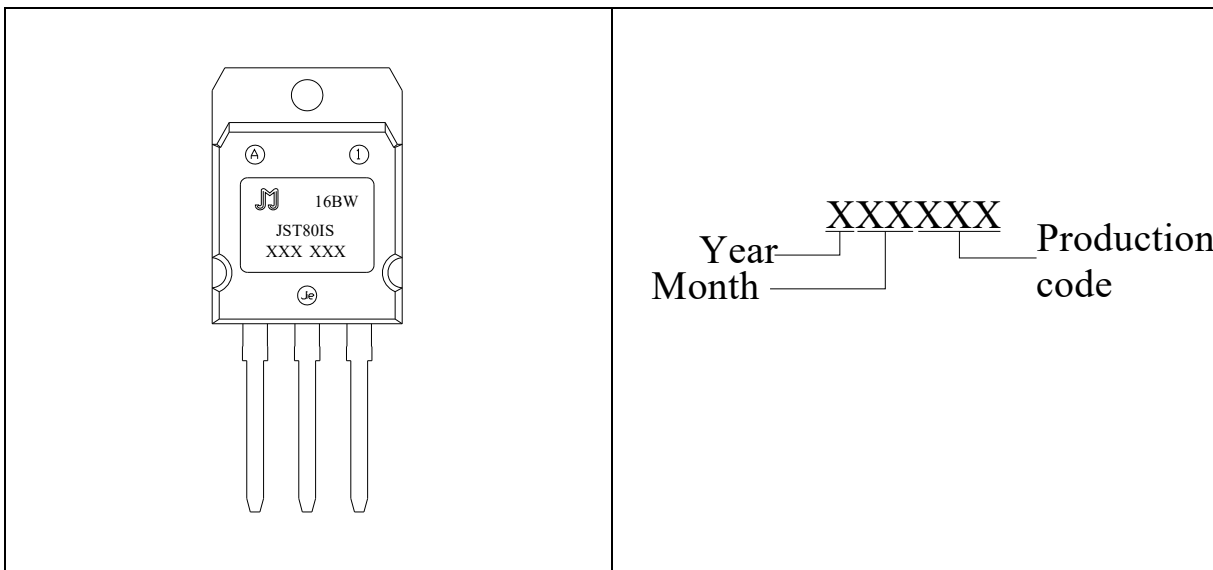


FIG.1: Maximum power dissipation versus RMS on-state current

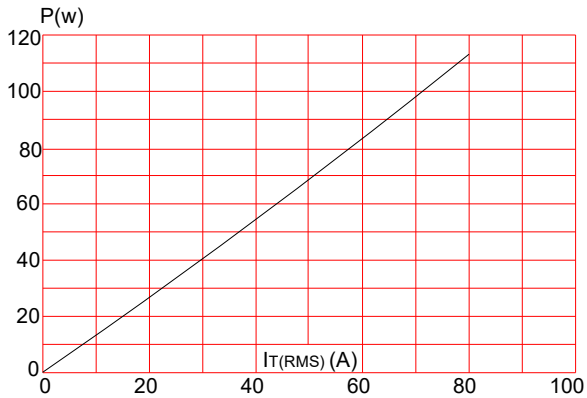


FIG.2: RMS on-state current versus case temperature

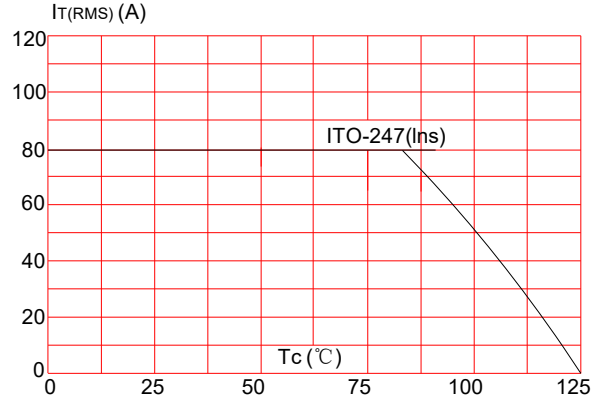


FIG.3: Surge peak on-state current versus number of cycles

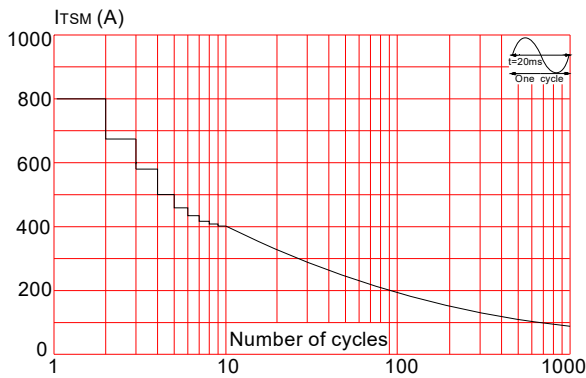


FIG.4: On-state characteristics (maximum values)

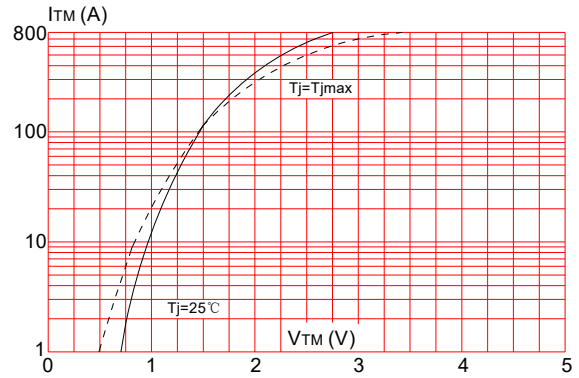


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

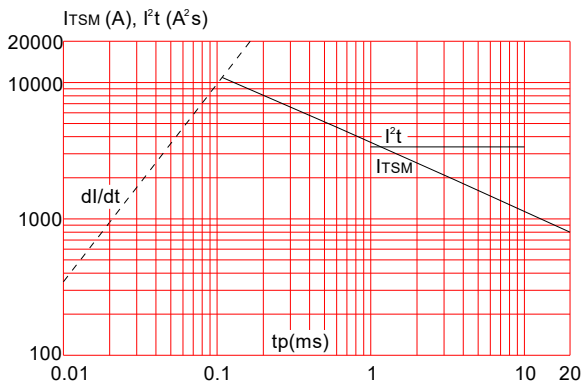
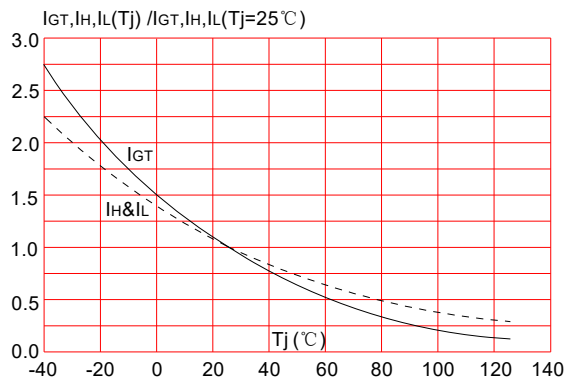


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



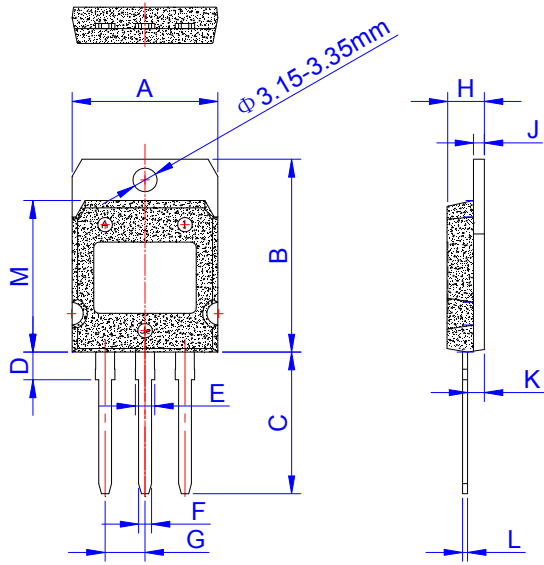
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JST80IS-1600BW	1600	50	ITO-247	25	Tube

Document Revision History

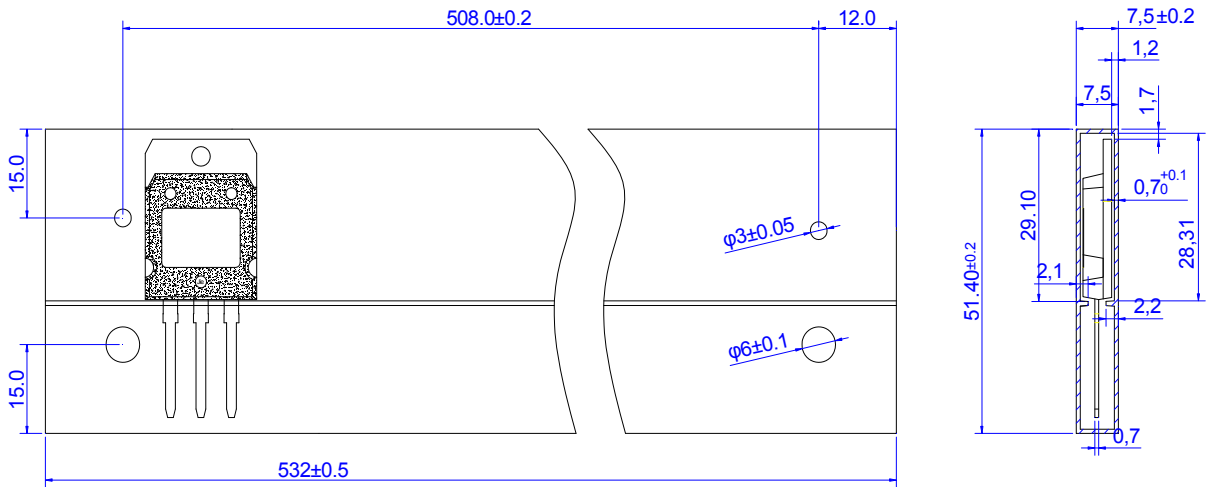
Date	Revision	Changes
Mar 18, 2022	1	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	19.7	19.9	20.1	0.776	0.783	0.791
B	26.9	27.1	27.3	1.059	1.067	1.075
C	19.4	19.9	20.4	0.764	0.783	0.803
D	3.80	3.90	4.00	0.150	0.154	0.157
E	2.56	2.66	2.76	0.101	0.105	0.109
F	1.66	1.76	1.86	0.065	0.069	0.073
G		5.45			0.215	
H	5.05	5.10	5.50	0.199	0.201	0.217
J	1.45	1.50	1.55	0.057	0.059	0.061
K	2.20	2.30	2.40	0.087	0.091	0.094
L	0.60	0.70	0.80	0.024	0.028	0.031
M	21.2	21.3	21.4	0.835	0.839	0.843


DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
ITO-247	TUBE	25	400	1,600



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